Ultrathin insulator films from first principles: a ground and excited-state perspective

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Contents

1 Insulator films: from basic research to technological applications **1**

2 Theoretical framework **8**
2.1 Density functional theory (DFT) 11
2.1.1 The exchange-correlation functional 14
2.1.2 Comparison of DFT results to experiments 15
2.2 Solving the Kohn-Sham equations: implementation and additional approximations 16
2.2.1 Plane-waves 16
2.2.2 Pseudopotentials 18
2.2.3 **k**-points 19
2.3 Many-body perturbation theory 20
2.3.1 Single-particle excitations in electron spectroscopy . . . 20
2.3.2 Hedin's equations and the GW approximation 24
2.3.3 The quasiparticle equation 26
2.3.4 GW implementation: the space-time method 28

3 GW for surfaces and thin films **32**
3.1 Repeated-slab approach 32
3.2 The long-range tail of W 34
3.2.1 **k**-point sampling and interaction cell 35
3.2.2 The computation of W in reciprocal space 36
3.2.3 Anisotropy in the screened interaction 37
3.3 Screening in slab systems 42
3.3.1 Dielectric model 42
3.3.2 Parallel **k**-point sampling 43
3.3.3 Periodic repetition in the repeated-slab approach . . . 52
3.4 Summary 56

4 Ultrathin oxides: representative surface models or unique films? 58
4.1 Introduction . . . 58
4.2 Properties of the bulk materials . . . 61
4.2.1 Sodium chloride . . . 61
4.2.2 α-Quartz . . . 62
4.2.3 α-Alumina . . . 64
4.2.4 Cubic hafnia . . . 65
4.2.5 Comparison of the oxides . . . 66
4.3 Substrate influence for silica films . . . 67
4.3.1 Atomic structure: the siloxane surface . . . 67
4.3.2 Electronic structure . . . 73
4.3.3 Comparison to UPS and MIES experiments . . . 76
4.3.4 How well do supported monolayer films model realistic surfaces? . . . 80
4.4 Thickness dependence in freestanding films . . . 81
4.4.1 α-Quartz . . . 82
4.4.2 α-Alumina . . . 86
4.4.3 Cubic hafnia . . . 89
4.5 Summary . . . 91

5 Excited-state perspectives of ultrathin films 94
5.1 Freestanding slabs . . . 96
5.2 NaCl films on Ge(001) . . . 101
5.2.1 Experimental situation . . . 101
5.2.2 Atomic structure of the interface . . . 103
5.2.3 G_0W_0 calculations . . . 107
5.3 Image effects in oxide films . . . 117
5.4 Summary . . . 120

6 Conclusions 121
6.1 Summary . . . 121
6.2 Outlook . . . 124

A Abbreviations 127

B Dielectric models 129
B.1 Image-charge method for dielectric layer models . . . 129
B.2 Connection to G_0W_0: the static COHSEX approximation . . . 132

C Ultrathin oxide films **135**
C.1 Alternative terminations for the α-quartz (0001) 135
C.2 Surface-projected density of states 137

D NaCl films **139**
D.1 Atomic orbital projections 139
D.2 NaCl: the character of the bulk conduction band 140
D.3 Structure of the NaCl/Ge(001) interface 144
D.4 STM simulations 146

E Computer code developments **149**
E.1 Green's function 150
E.2 Block inversion of Hermitean packed matrices 152
E.3 Disk storage 155
E.4 Efficient computation of the matrix elements of $\mathbf{r}$ 157

F Computational parameters **160**
F.1 Pseudopotentials 160
F.2 DFT-LDA calculations 160
F.3 G_0W_0 calculations 161
F.3.1 Time-frequency grids 161
F.3.2 System-dependent convergence parameters 161
F.3.3 Band cutoff 162

Bibliography **165**